



PRELIMINARY

SOLID STATE DEVICES, INC.

14005 Stage Road * Santa Fe Springs, Ca 90670

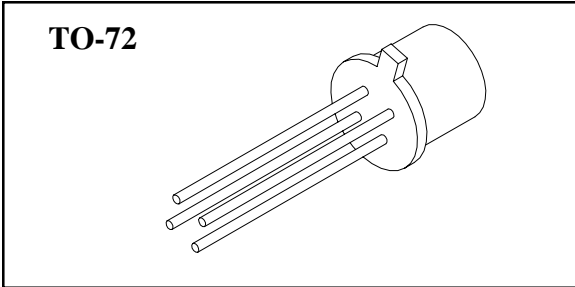
Phone: (562) 404-4474 * Fax: (562) 404-1773

SFT4959

**30mA
18 VOLTS
PNP TRANSISTOR**

Designer's Data Sheet

- FEATURES:**
- PNP Silicon Annular Transistor
 - High Speed
 - High Frequency
 - Low Noise



Maximum Ratings	SYMBOL	VALUE	UNITS
Collector-Emitter Voltage	V_{CEO}	18	Volts
Collector-Base Voltage	V_{CBO}	25	Volts
Emitter-Base Voltage	V_{EBO}	3	Volts
Collector Current	I_C	30	mA
Total Device Dissipation @ $T_C=100^{\circ}C$ Derate above $100^{\circ}C$	P_D	.2 1.14	W mW/ $^{\circ}C$
Operating and Storage Temperature	T_J, T_{STG}	-65 to +200	$^{\circ}C$
Thermal Resistance, Junction to Case	$R_{\theta JC}$.87	$^{\circ}C/mW$

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0001A

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Electrical Characteristics *	SYMBOL	MIN	MAX	UNITS
Collector-Emitter Breakdown Voltage ($I_C = 1\text{mA}_{dc}$)	BV_{CEO}	18	-	V
Collector-Base Breakdown Voltage ($I_C = 0.1\text{mA}_{dc}$)	BV_{CBO}	25	-	V
Emitter-Base Breakdown Voltage ($I_E = 0.1\text{mA}_{dc}$)	BV_{EBO}	3	-	V
Collector Cutoff Current ($V_{CB} = 10\text{V}_{dc}$)	I_{CBO}	-	0.1	μA
Forward Current Transfer Ratio ($I_C = 2\text{mA}$, $V_{CE} = 10\text{V}_{dc}$)	h_{FE}	20	200	
Current Gain Bandwidth Product ($I_C = 10\text{mA}$, $V_{CE} = 10\text{V}_{dc}$, $f = 100\text{ MHz}$)	f_T	1000	-	MHz
Collector-Base Capacitance ($V_{CB} = 10\text{ V}_{dc}$, $I_E = 0$, $f = 1\text{ MHz}$)	C_{ob}	-	0.8	pF

* $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

CASE OUTLINE: TO-72

- PIN 1: EMITTER**
- PIN 2: BASE**
- PIN 3: COLLECTOR**
- PIN 4: CASE**

